



BENHA UNIVERSITY  
FACULTY OF ENGINEERING AT SHOUBRA

**ECE-291**  
**Electronic Engineering**

Part II,  
Lecture #1  
Electronics Applications & Diodes

**Instructor:**  
**Dr. Ahmad El-Banna**



# Agenda

- Part II Objectives
- Part II Information
- Lectures List
- Electronics Fundamentals
- Electronics Applications
- Intro. to Diodes

# Part II Objectives

**Remember:**  
**Part I: Electric Circuits**  
**Part II: Electronic Circuits**

- ***Understand the fundamentals of electronics and know its applications.***
- ***Being familiar with diodes and regulator circuits.***
- ***Know the different types of transistors and analyze their circuits.***
- ***Understand Modulation Circuits.***
- ***Understand the Logic and digital circuits and study some of their applications.***



# Part II Information

<b>Instructor:</b>	Dr. Ahmad El-Banna <a href="http://bu.edu.eg/staff/ahmad.elbanna">http://bu.edu.eg/staff/ahmad.elbanna</a> Office: Room # SB-205 Email: <a href="mailto:ahmad.elbanna@feng.bu.edu.eg">ahmad.elbanna@feng.bu.edu.eg</a>
<b>Lectures:</b>	Thursday: 12:30-15:30
<b>Office Hours:</b>	Saturday, Sunday, Wednesday (14:00~16:30) Thursday (11:00 ~12:30)
<b>T.A.:</b>	Eng. Mohamed El-Sayed
<b>Texts/Notes:</b>	<ul style="list-style-type: none"><li>• Lectures slides, available by each lecture, and found online at <a href="http://bu.edu.eg/staff/ahmad.elbanna-courses/12136">http://bu.edu.eg/staff/ahmad.elbanna-courses/12136</a></li><li>• T. Floyd, <b>Electronic devices</b> - Conventional Current Version, 9<sup>th</sup> edition, Prentice Hall.</li></ul>
<b>Course Credit:</b>	150 Marks (75 mark/part)
<b>Part II Grading:</b>	<ul style="list-style-type: none"><li>▪ <b>45 Marks</b><ul style="list-style-type: none"><li>• Final Exam (Closed-Book)</li></ul></li><li>▪ <b>30 Marks</b><ul style="list-style-type: none"><li>• Mid Term Exam (Open-Book! ) (10)</li><li>• Oral Exam (8)</li><li>• Project (7)</li><li>• Tutorials Activities (5)</li></ul></li></ul>



# Lectures List

Week#1

- Introduction and Electronics Applications

Week#2

- Diodes and Regulation Circuits

Week#3

- Basics of Transistors

Week#4

- Transistor circuits analysis & Applications

Week#5

- Modulation Circuits

Week#6

- Logic and Digital Circuits

Week#7

- M.T. Exam & Project Delivery



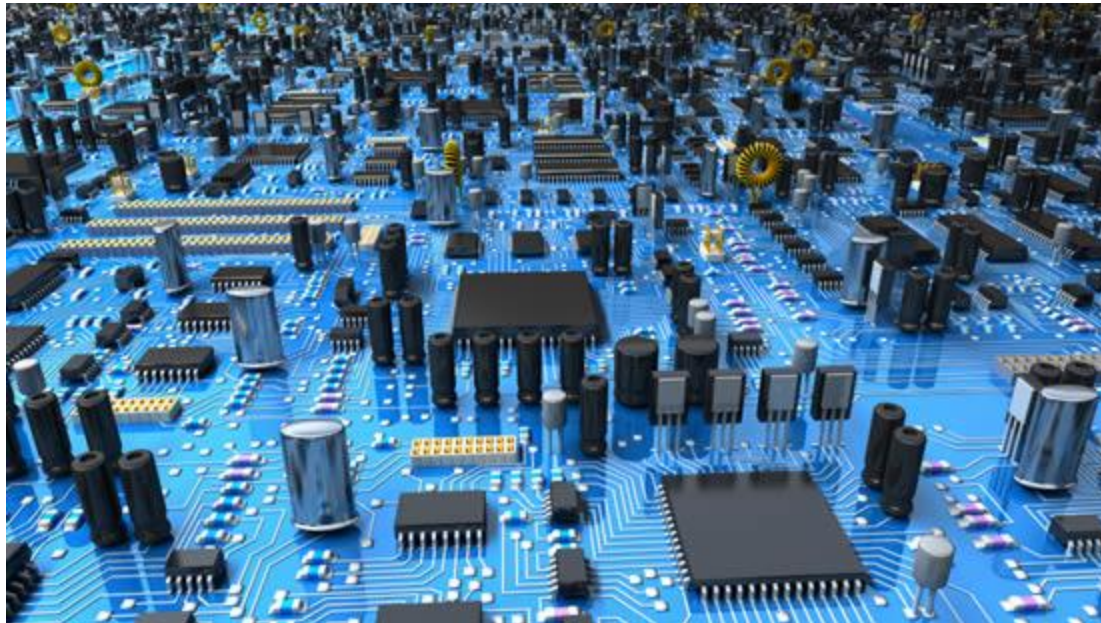
# ELECTRONICS APPLICATIONS



( 6 )

# Meaning of Electronics

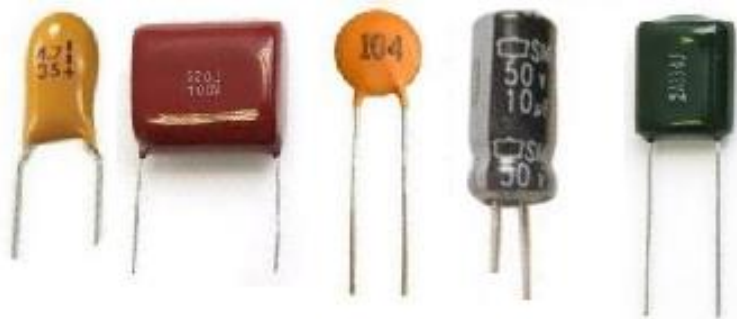
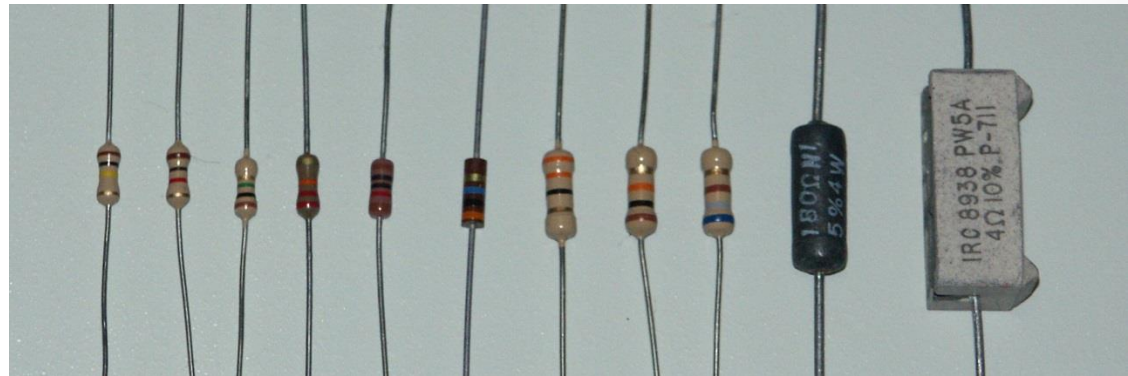
- Electronics means study of flow of electrons in electrical circuits.
- All electronic circuits contain few basic components.
- That are three passive components and two active components.
- An Integrated circuit may comprise of thousands of transistors, few capacitors on a small chip.



# Types of Electronic Components..

- *Passive Components*

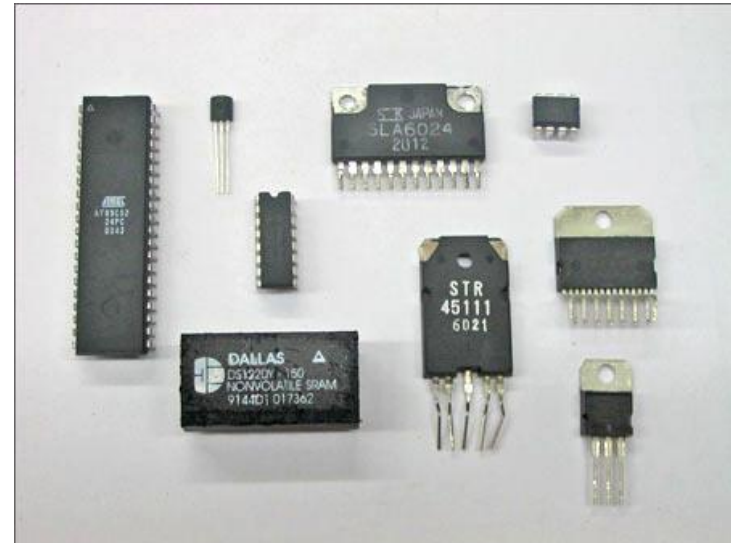
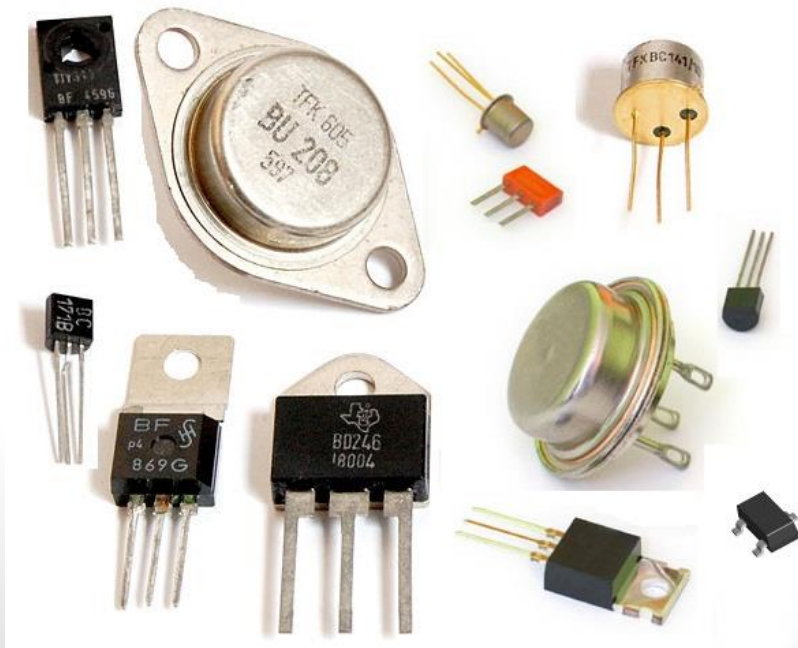
- Resistors
- Capacitors
- Inductors





# Types of Electronic Components

- *Active Components*
  - Tube devices
  - Semiconductor devices



# Electronics Applications

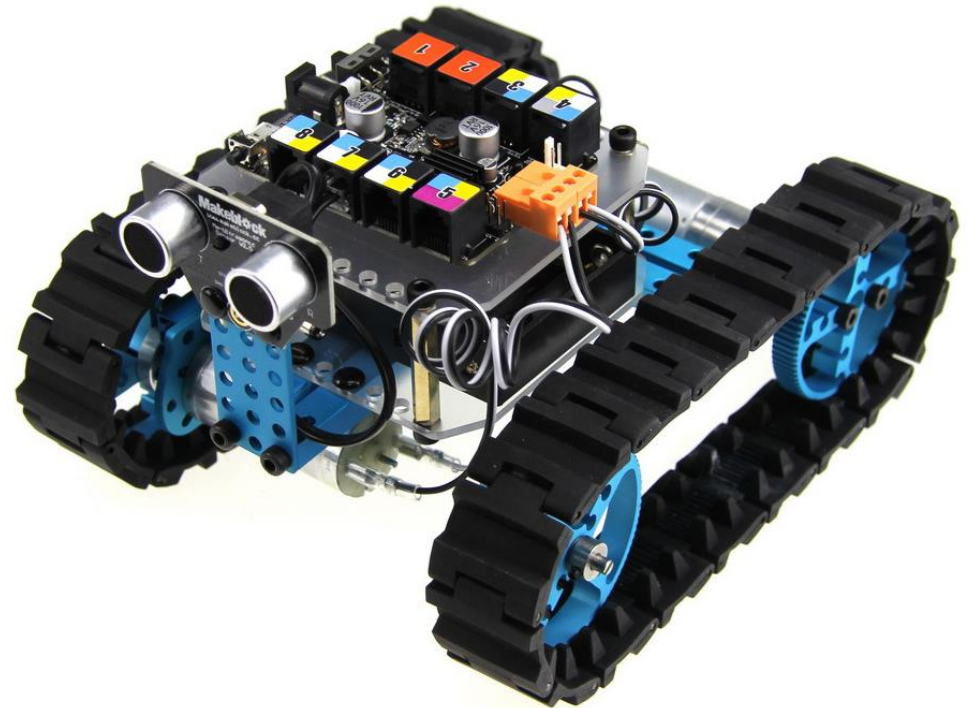
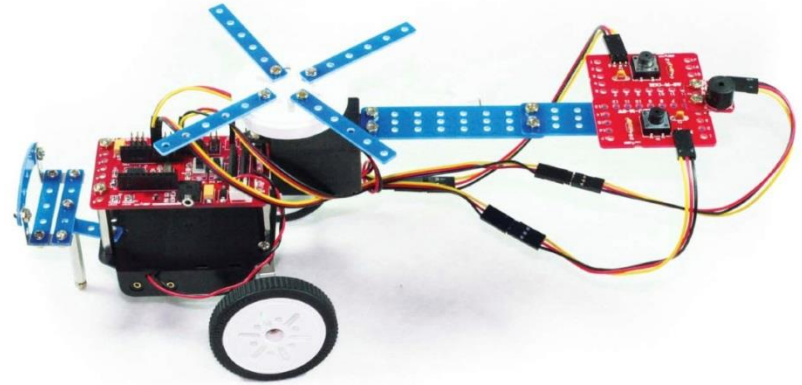
- Look around you !
- You will find it everywhere



# Electronics Applications..



# Electronics Applications...



# Electronics Applications....



and more and more 😊



# ELECTRONICS FUNDAMENTALS



# MATERIALS USED IN ELECTRONICS

- Insulators

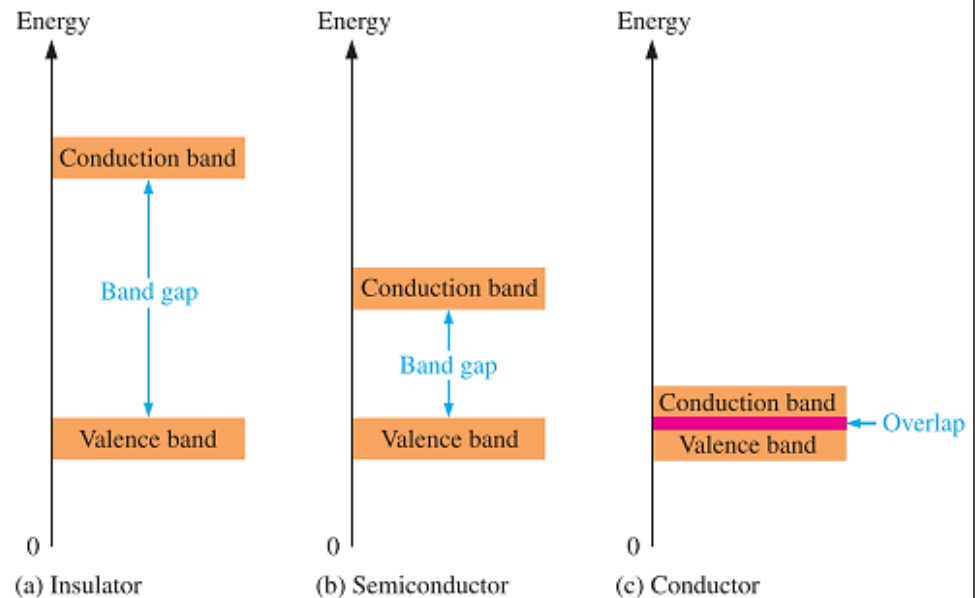
- An insulator is a material that does not conduct electrical current under normal conditions.

- Conductors

- A conductor is a material that easily conducts electrical current.
- Most metals are good conductors.

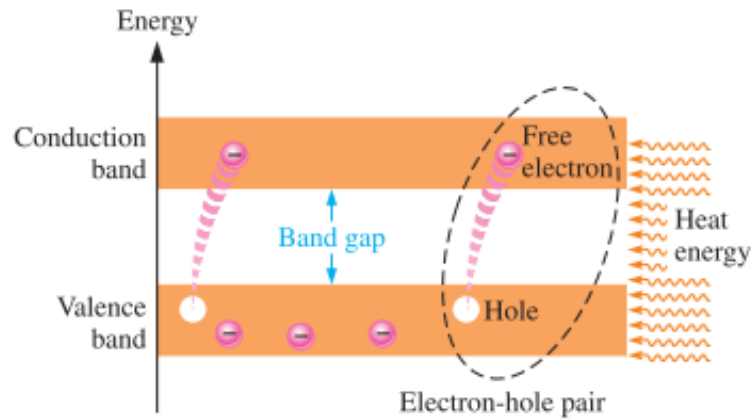
- Semiconductors

- A semiconductor is a material that is between conductors and insulators in its ability to conduct electrical current.

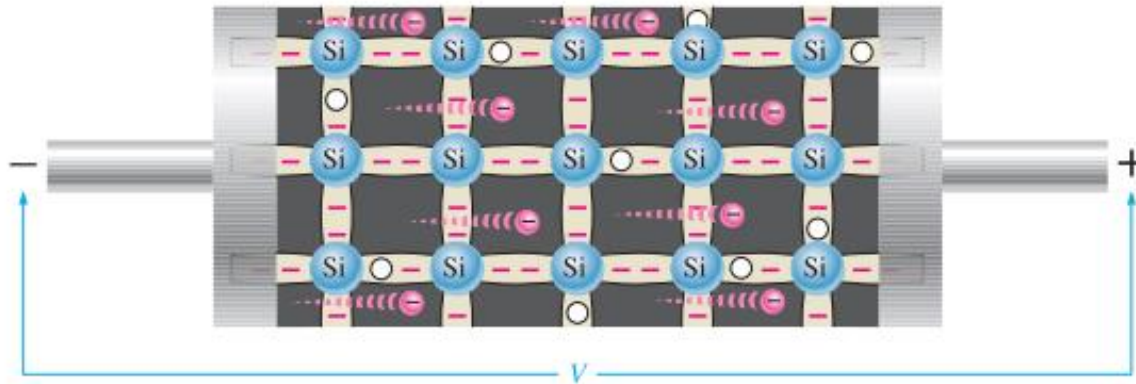


# CURRENT IN SEMICONDUCTORS

- Creation of electron-hole pairs in a silicon crystal.
- Electrons in the conduction band are free electrons.



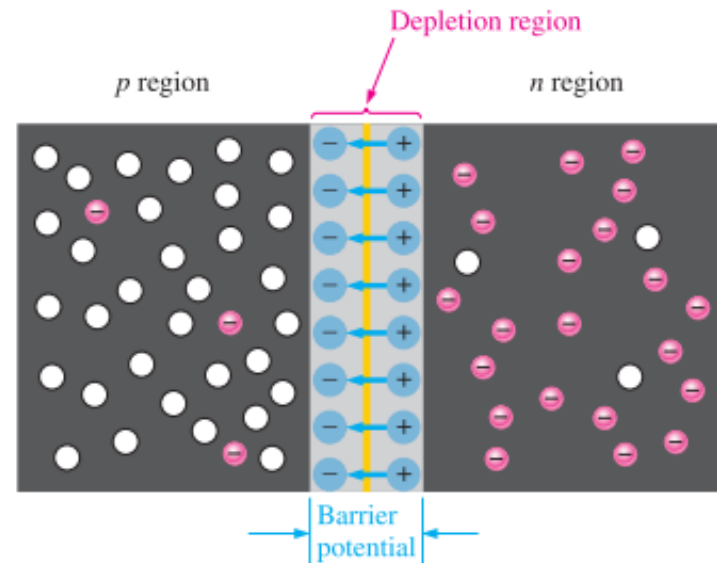
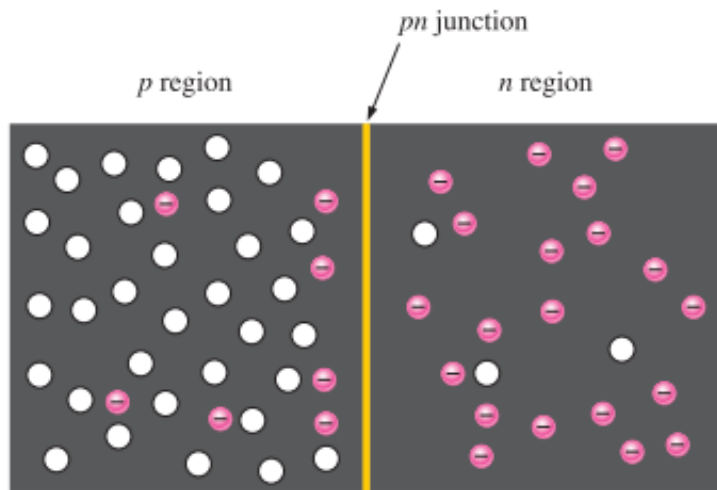
- Electron current in intrinsic silicon is produced by the movement of thermally generated free electrons.





# PN Junction

- N-Type Semiconductor
  - The electrons are the majority carriers and the holes are the minority. This is done by doping process.
- P-Type Semiconductor
  - The holes are the majority carriers and the electrons are the minority.



- The basic silicon structure at the instant of junction formation showing only the majority and minority carriers.

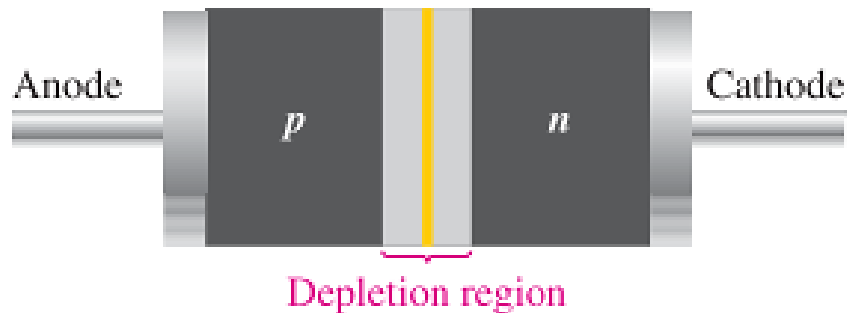
- electrons diffuse and a depletion region is formulated.

# DIODES



# Diodes

- A diode is made from a small piece of semiconductor material, usually silicon, in which half is doped as a **p** region and half is doped as an **n** region with a **pn** junction and depletion region in between.

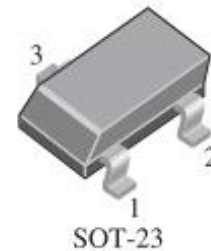
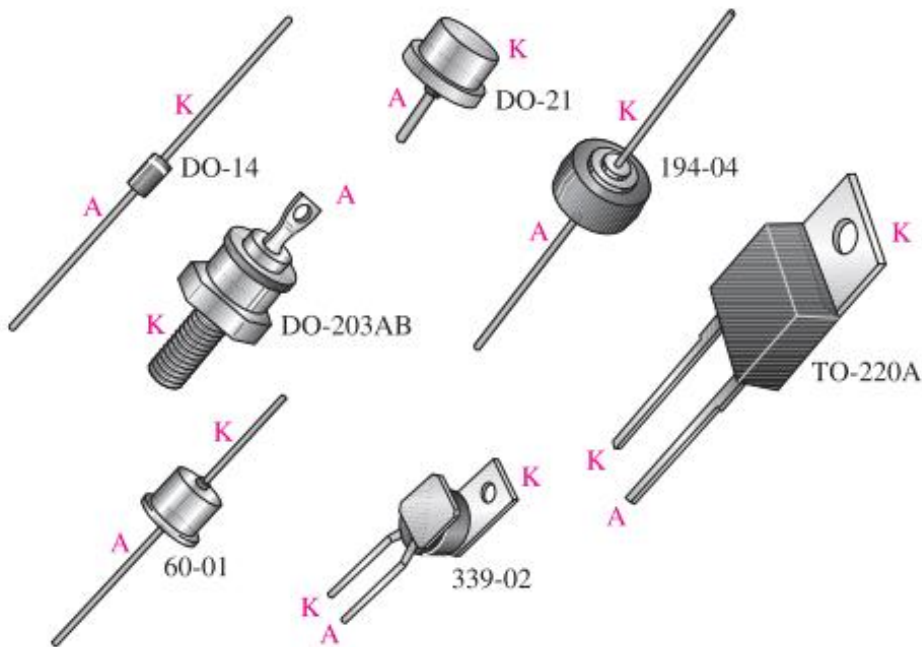


Basic structure



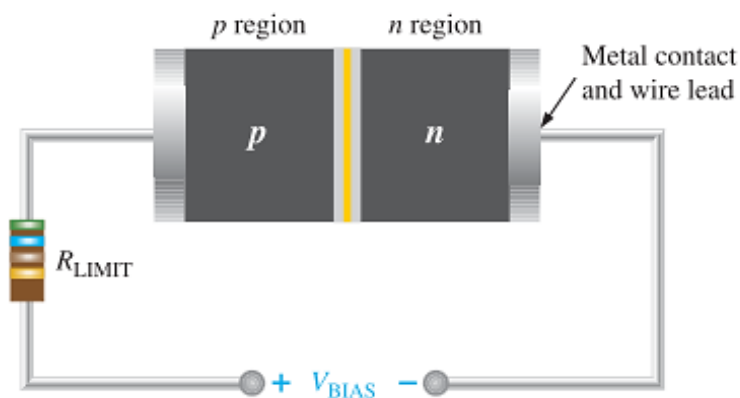
Symbol

# Diode Packages

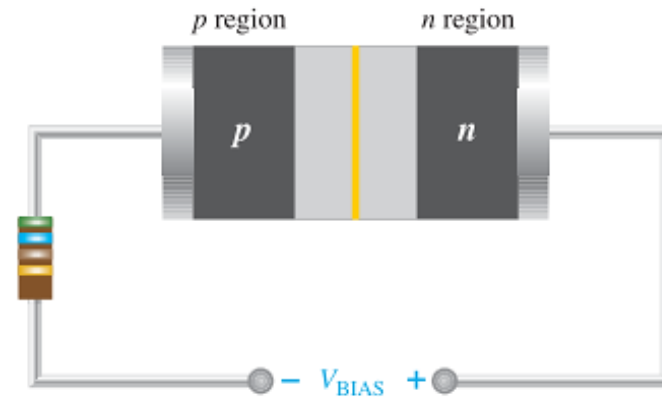


# Forward & Reverse Bias

- To **bias** a diode, you apply a dc voltage across it.
- **Forward bias** is the condition that **allows current** through the pn junction.
- **Reverse bias** is the condition that essentially **prevents current** through the diode.



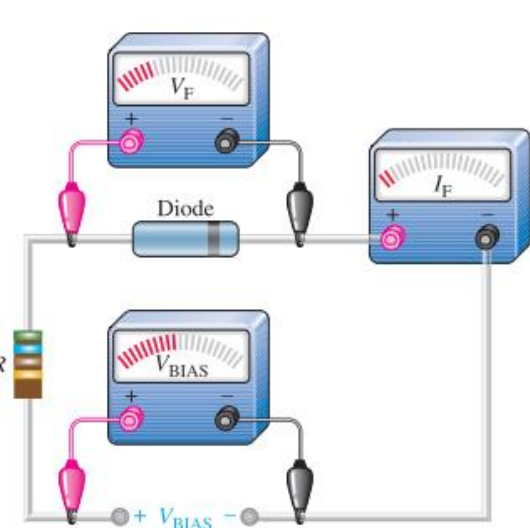
Forward bias



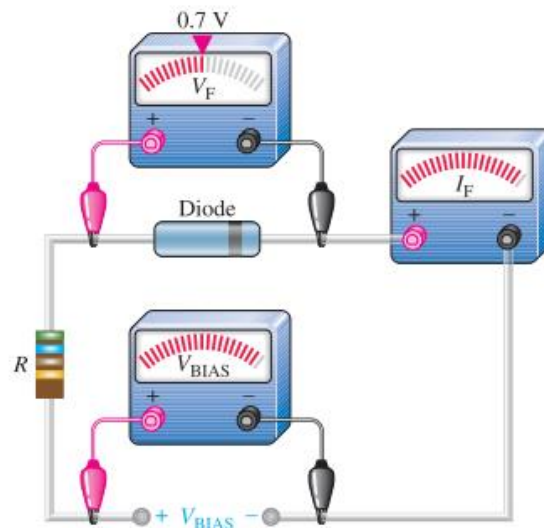
Reverse bias

# VOLTAGE-CURRENT CHARACTERISTIC OF A DIODE

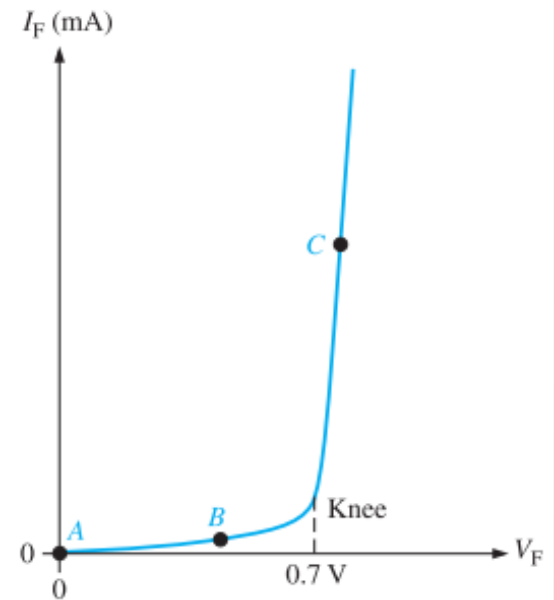
- V-I Characteristic for Forward Bias



(a) Small forward-bias voltage ( $V_F < 0.7$  V), very small forward current.

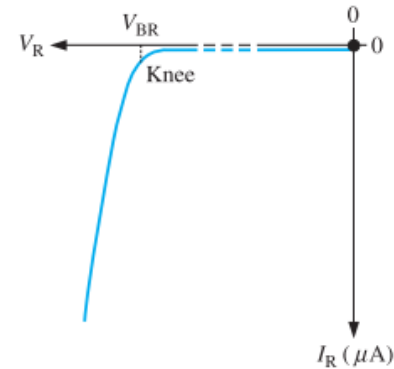


(b) Forward voltage reaches and remains nearly constant at approximately 0.7 V. Forward current continues to increase as the bias voltage is increased.

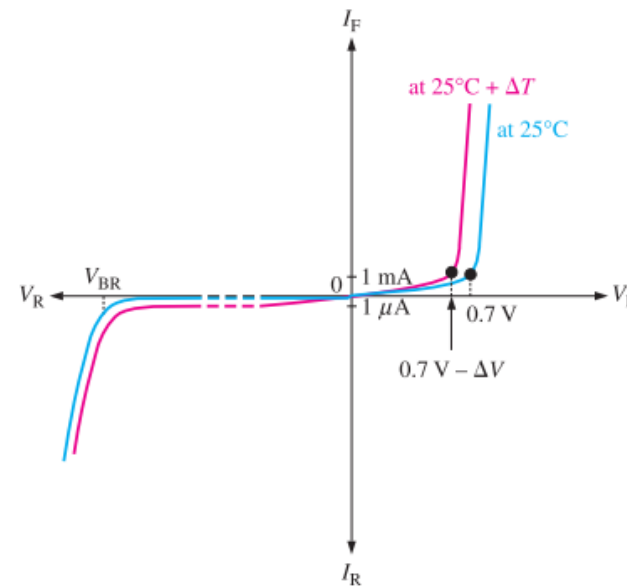
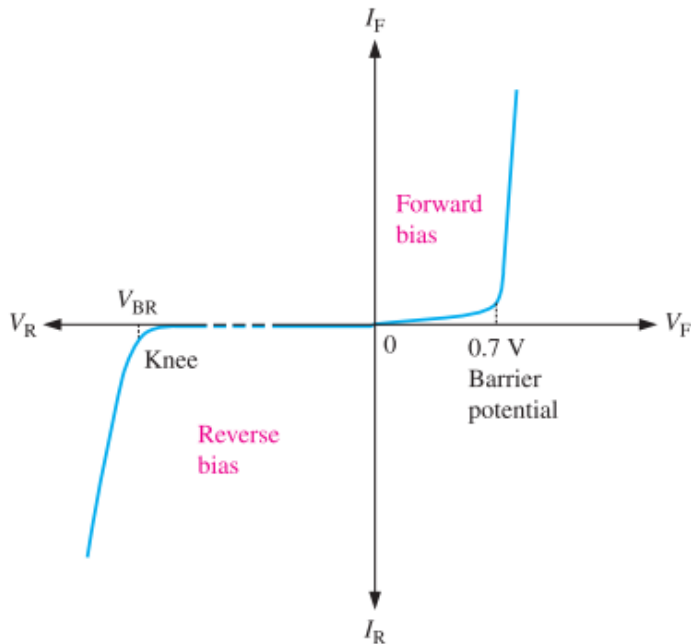


# V-I CHARACTERISTIC OF A DIODE ..

- V-I Characteristic for Reverse Bias



- Complete V-I Characteristic

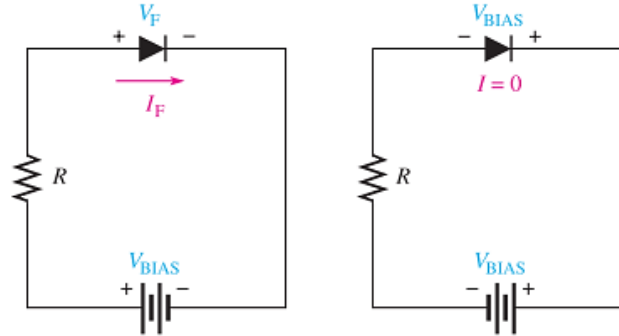


Temperature Effect



# DIODE MODELS

- Bias Connections

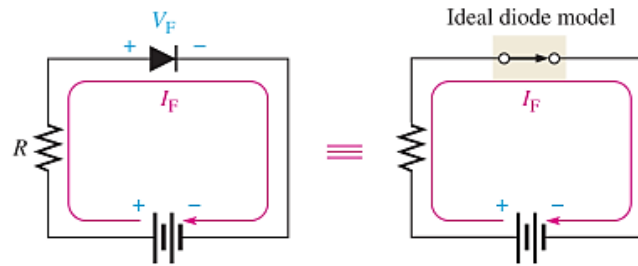


(a) Forward bias

(b) Reverse bias

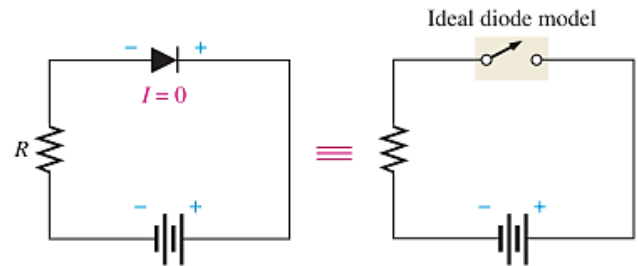
## 1. The Ideal Diode Model

$$V_F = 0 \text{ V} \quad I_F = \frac{V_{\text{BIAS}}}{R_{\text{LIMIT}}}$$

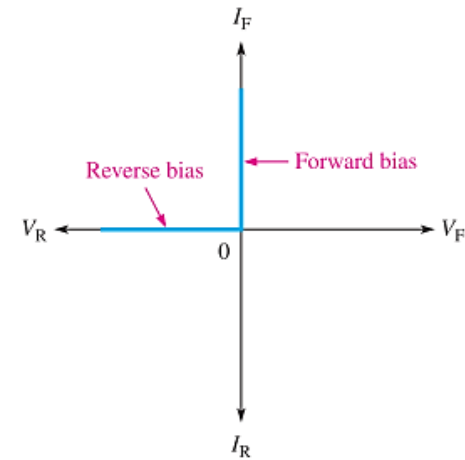


(a) Forward bias

$$I_R = 0 \text{ A} \quad V_R = V_{\text{BIAS}}$$



(b) Reverse bias



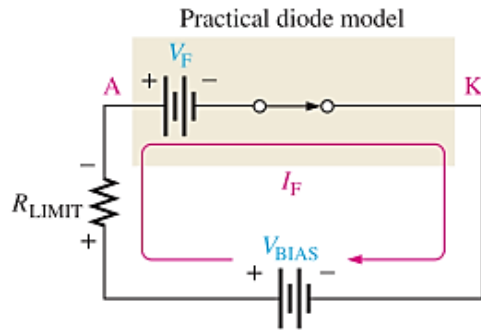
(c) Ideal  $V$ - $I$  characteristic curve (blue)



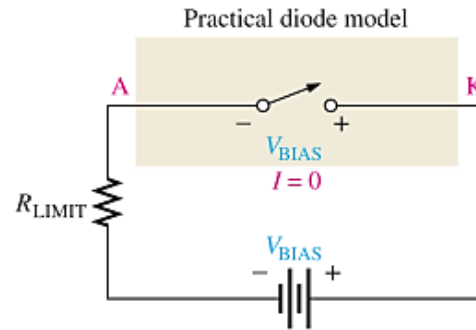


# DIODE MODELS..

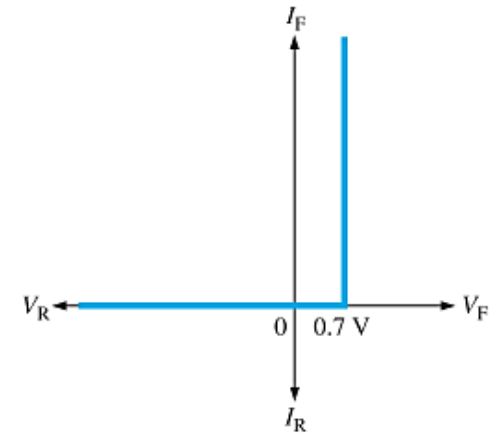
## 2. The Practical Diode Model



(a) Forward bias



(b) Reverse bias



(c) Characteristic curve (silicon)

$$V_F = 0.7 \text{ V}$$

$$V_{BIAS} - V_F - V_{R_{LIMIT}} = 0$$

$$V_{R_{LIMIT}} = I_F R_{LIMIT}$$

$$I_F = \frac{V_{BIAS} - V_F}{R_{LIMIT}}$$

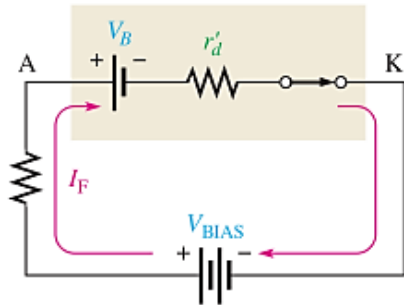
$$I_R = 0 \text{ A}$$

$$V_R = V_{BIAS}$$

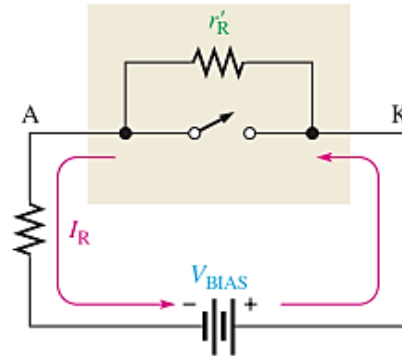


# DIODE MODELS..

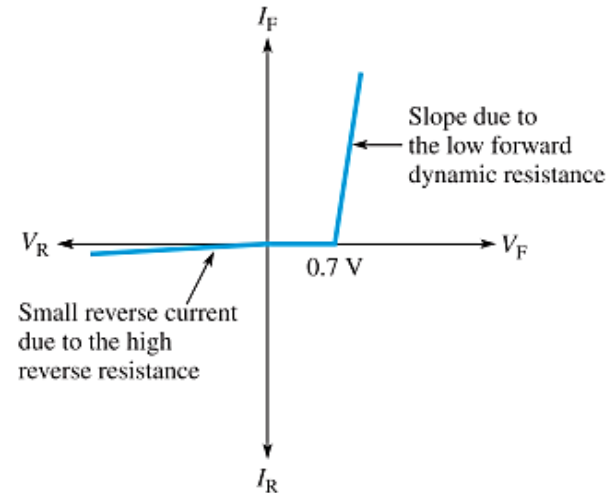
## 3. The Complete Diode Model



(a) Forward bias



(b) Reverse bias



(c) V-I characteristic curve

$$V_F = 0.7 \text{ V} + I_F r'_d$$

$$I_F = \frac{V_{\text{BIAS}} - 0.7 \text{ V}}{R_{\text{LIMIT}} + r'_d}$$

$I_R$  : Reverse (leakage) current  $\rightarrow$  diode datasheet

$$V_R = I_R r'_R$$

- For more details, refer to:
  - Chapter 1&2, T. Floyd, **Electronic Devices and Circuit Theory**, 11<sup>th</sup> edition, Prentice Hall.
- The lecture is available online at:
  - <http://bu.edu.eg/staff/ahmad.elbanna-courses/12136>
- For inquires, send to:
  - [ahmad.elbanna@feng.bu.edu.eg](mailto:ahmad.elbanna@feng.bu.edu.eg)